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Kind regards,

Team Nexperia



1 A low V_F dual MEGA Schottky barrier rectifierRev. 1 — 25 August 2010Pr

Product data sheet

Product profile 1.

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier in common cathode configuration with an integrated guard ring for stress protection, encapsulated in a SOT1061 leadless small Surface-Mounted Device (SMD) plastic package with medium power capability.

1.2 Features and benefits

- Average forward current: I_{F(AV)} ≤ 1 A
- Reverse voltage: V_R ≤ 60 V
- Low forward voltage
- Exposed heat sink (cathode pad) for excellent thermal and electrical conductivity
- Leadless small SMD plastic package with medium power capability
- AEC-Q101 qualified

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch Mode Power Supply (SMPS)
- Reverse polarity protection
- Low power consumption applications
- Battery chargers for mobile equipment

1.4 Quick reference data

Table 1. Quick reference data

 $T_i = 25 \ ^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode						
I _{F(AV)}	average forward current	square wave; δ = 0.5; f = 20 kHz				
		$T_{amb} \le 110 \ ^{\circ}C$	<u>[1]</u> -	-	1	А
		$T_{sp} \le 140 \ ^{\circ}C$	-	-	1	А
V _R	reverse voltage		-	-	60	V
V _F	forward voltage	I _F = 1 A	-	490	540	mV
I _R	reverse current	V _R = 60 V	-	33	100	μA

[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.



1 A low V_F dual MEGA Schottky barrier rectifier

2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	anode diode 1		
2	anode diode 2	3	3
3	common cathode		
		Transparent top view	006aaa438

3. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
PMEG6010CPA	HUSON3	plastic thermal enhanced ultra thin small outline package; no leads; three terminals; body $2 \times 2 \times 0.65$ mm	SOT1061		

4. Marking

Table 4. Mark	ing codes	
Type number		Marking code
PMEG6010CPA		AP

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		0, (,		
Symbol	Parameter	Conditions	Min	Max	Unit
Per diode					
V _R	reverse voltage	$T_j \le 25 \ ^\circ C$	-	60	V
I _{F(AV)}	average forward current	square wave; δ = 0.5; f = 20 kHz			
		$T_{amb} \le 110 \ ^{\circ}C$	<u>[1]</u> -	1	А
		$T_{sp} \le 140 \ ^{\circ}C$	-	1	А
I _{FRM}	repetitive peak forward current	$t_p \le 1 \text{ ms}; \delta \le 0.25$	-	7	A
I _{FSM}	non-repetitive peak forward current	square wave; t _p = 8 ms	<u>[2]</u> _	9	A

1 A low V_F dual MEGA Schottky barrier rectifier

Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per device, or	ne diode loaded				
P_{tot} total power dissipation $T_{amb} \le$		$T_{amb} \le 25 \ ^{\circ}C$	[3][4]	500	mW
			[3][5]	960	mW
			<u>[1][3]</u> _	1800	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

[2] $T_i = 25 \,^{\circ}C$ prior to surge.

[3] Reflow soldering is the only recommended soldering method.

[4] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[5] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per devic	e, one diode loaded					
R _{th(j-a)}	thermal resistance from	in free air	[1][2]			
	junction to ambient		[3] _	-	250	K/W
			[4] _	-	130	K/W
			[5] _	-	70	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		<u>[6]</u> _	-	12	K/W

[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_B are a significant part of the total power losses.

[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

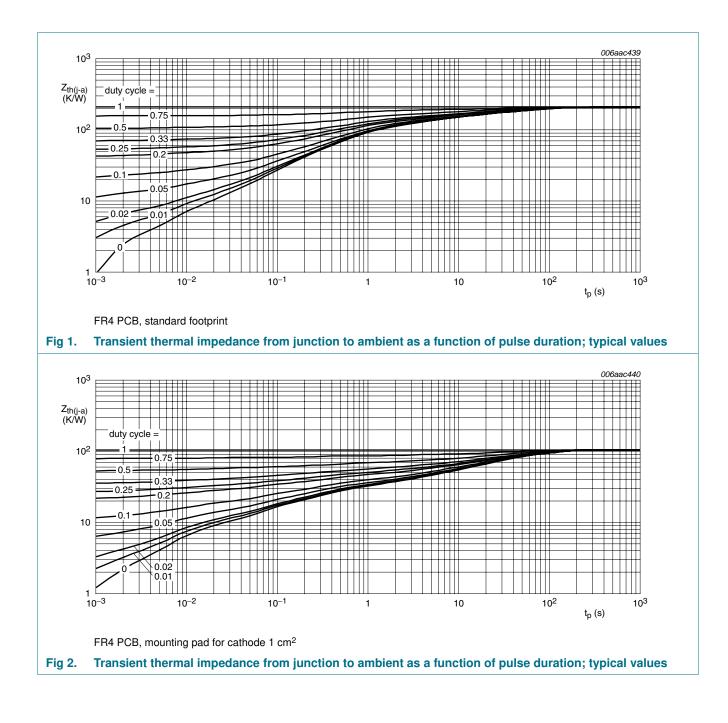
[5] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

[6] Soldering point of cathode tab.

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PMEG6010CPA

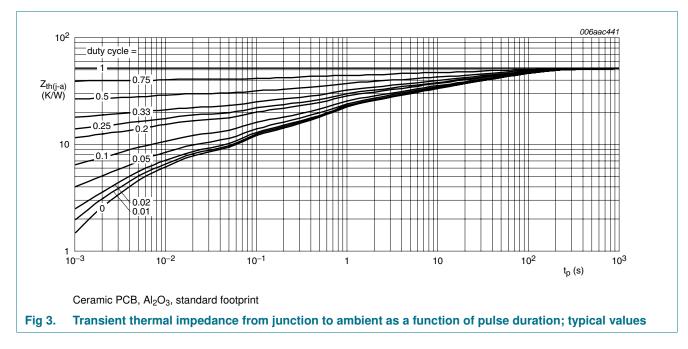
1 A low V_F dual MEGA Schottky barrier rectifier



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1 A low V_F dual MEGA Schottky barrier rectifier



7. Characteristics

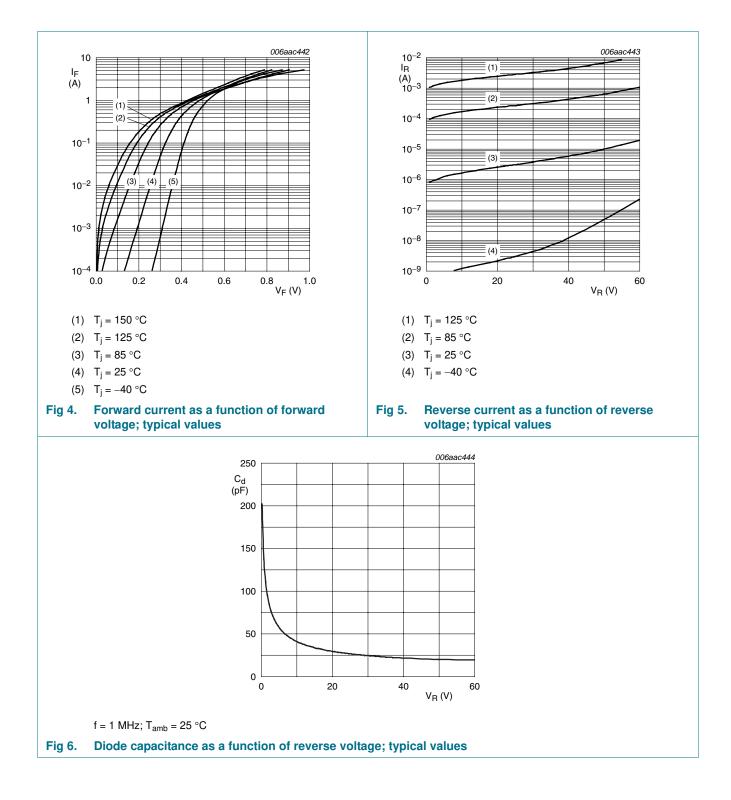
Table 7.Characteristics

$T_i =$	25	°C	unless	other	wise	specified.
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode						
V _F	forward voltage	I _F = 100 mA	-	325	-	mV
		$I_F = 1 A$	-	490	540	mV
I _R reverse curre	reverse current	V _R = 10 V	-	2	-	μA
		V _R = 60 V	-	33	100	μA
C _d	diode capacitance	f = 1 MHz				
		$V_{R} = 1 V$	-	120	-	pF
		V _R = 10 V	-	40	-	pF
t _{rr}	reverse recovery time	9	[1] -	40	-	ns

[1] When switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA.

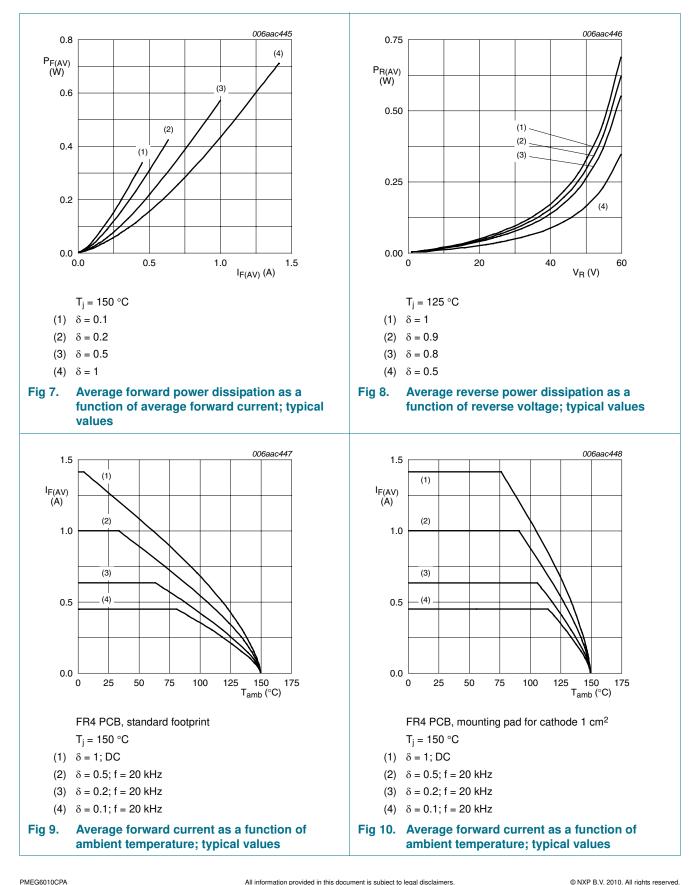
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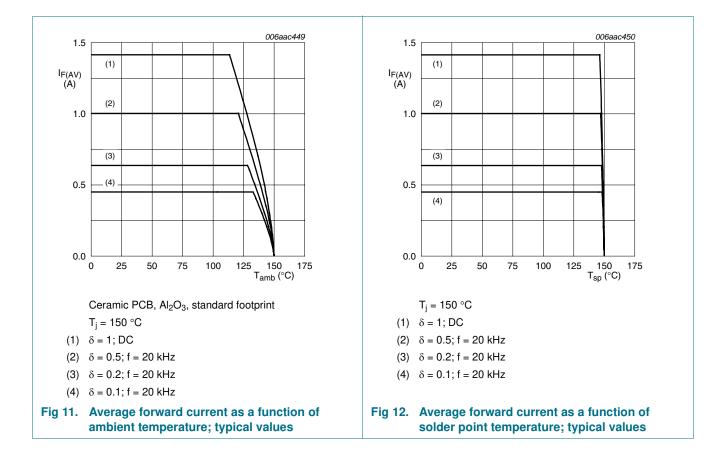
PMEG6010CPA

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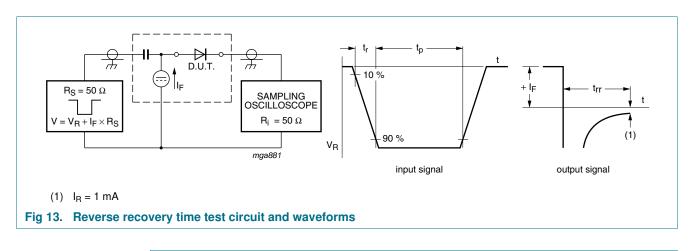
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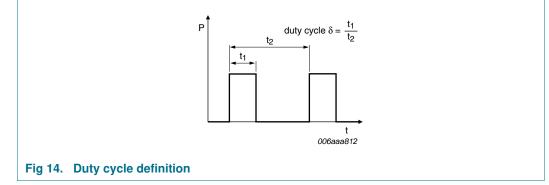
1 A low V_F dual MEGA Schottky barrier rectifier



1 A low V_F dual MEGA Schottky barrier rectifier

8. Test information





The current ratings for the typical waveforms as shown in Figure 9, 10, 11 and 12 are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current,

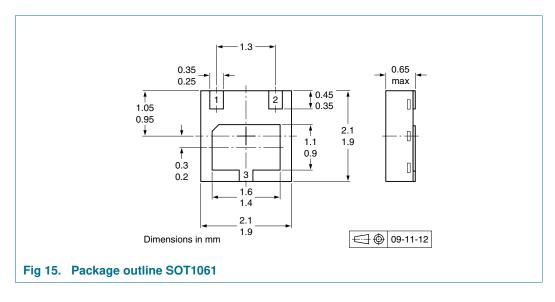
 $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

1 A low V_F dual MEGA Schottky barrier rectifier

9. Package outline



10. Packing information

Table 8. Packing methods

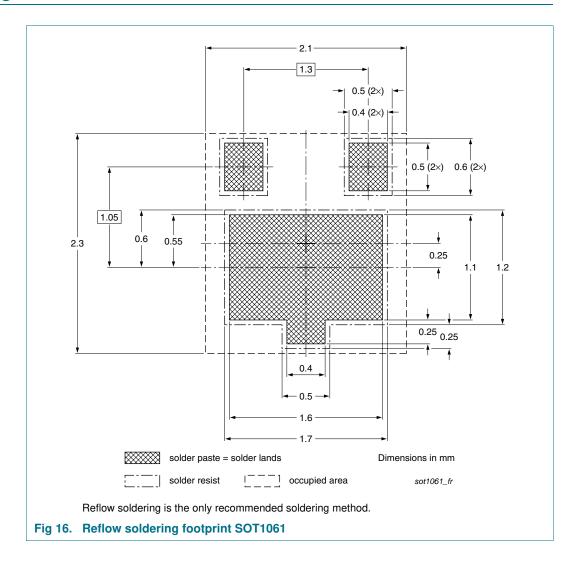
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity
			3000
PMEG6010CPA	SOT1061	4 mm pitch, 8 mm tape and reel	-115

[1] For further information and the availability of packing methods, see Section 14.

1 A low V_F dual MEGA Schottky barrier rectifier

11. Soldering



PMEG6010CPA Product data sheet

1 A low V_F dual MEGA Schottky barrier rectifier

12. Revision history

Table 9. Revision hist	ory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEG6010CPA v.1	20100825	Product data sheet	-	-

1 A low V_F dual MEGA Schottky barrier rectifier

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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1 A low V_F dual MEGA Schottky barrier rectifier

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1 A low V_F dual MEGA Schottky barrier rectifier

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